PD - 96372

International Rectifier

IRFI4410ZGPbF

HEXFET® Power MOSFET

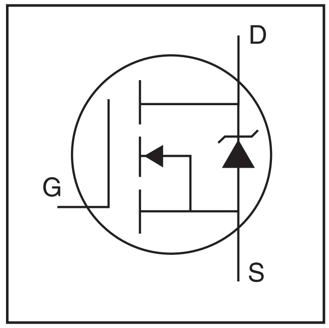
Applications

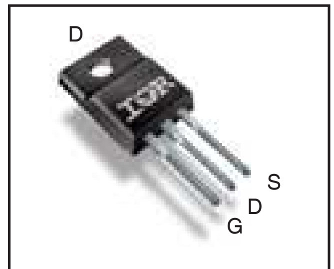
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

V_{DSS}		**100V**
$R_{DS(on)}$	typ.	**7.9mΩ**
	max.	**9.3mΩ**
I_D		**43A**

Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free
- Halogen-Free





TO-220AB Full-Pak

G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	43	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	30	
I_{DM}	Pulsed Drain Current ①	170	
P_D @T_C = 25°C	Maximum Power Dissipation	47	W
	Linear Derating Factor	0.3	W/°C
V_{GS}	Gate-to-Source Voltage	±30	V
$E_{AS\ (Thermally\ limited)}$	Single Pulse Avalanche Energy ②	310	mJ
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	——	3.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④	——	65	

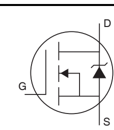
Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	–––	–––	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	95	–––	mV/°C	Reference to 25°C, I_D = 5mA ③
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	7.9	9.3	m	V_{GS} = 10V, I_D = 26A ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	–––	4.0	V	V_{DS} = V_{GS}, I_D = 150μA
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	20	μA	V_{DS} = 100V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 100V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -20V
$R_{G(int)}$	Internal Gate Resistance	–––	0.9	–––		

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	80	–––	–––	S	V_{DS} = 50V, I_D = 26A
Q_g	Total Gate Charge	–––	81	110	nC	I_D = 26A
Q_{gs}	Gate-to-Source Charge	–––	18	–––		V_{DS} = 50V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	23	–––		V_{GS} = 10V ③
$t_{d(on)}$	Turn-On Delay Time	–––	15	–––	ns	V_{DD} = 65V
t_r	Rise Time	–––	27	–––		I_D = 26A
$t_{d(off)}$	Turn-Off Delay Time	–––	43	–––		R_G = 2.7
t_f	Fall Time	–––	30	–––		V_{GS} = 10V ③
C_{iss}	Input Capacitance	–––	4910	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	330	–––		V_{DS} = 50V
C_{rss}	Reverse Transfer Capacitance	–––	150	–––		ƒ = 1.0MHz
C_{oss} eff. (ER)	Effective Output Capacitance (Energy Related)	–––	420	–––		V_{GS} = 0V, V_{DS} = 0V to 80V ⑥, See Fig.11
C_{oss} eff. (TR)	Effective Output Capacitance (Time Related)	–––	680	–––		V_{GS} = 0V, V_{DS} = 0V to 80V ⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	43	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	170	A	
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	T_J = 25°C, I_S = 26A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	–––	47	71	ns	T_J = 25°C V_R = 85V,
		–––	54	81		T_J = 125°C I_F = 26A
Q_{rr}	Reverse Recovery Charge	–––	110	160	nC	T_J = 25°C di/dt = 100A/μs ③
		–––	140	210		T_J = 125°C
I_{RRM}	Reverse Recovery Current	–––	2.5	–––	A	T_J = 25°C
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.91mH R_G = 25Ω, I_{AS} = 26A, V_{GS} =10V. Part not recommended for use above this value.

③ Pulse width ≤ 400μs; duty cycle ≤ 2%.

④ R_θ is measured at T_J approximately 90°C

⑤ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

⑥ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

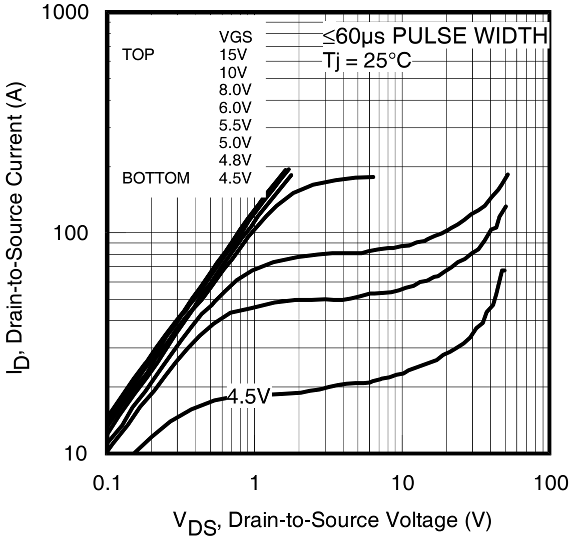


Fig 1. Typical Output Characteristics

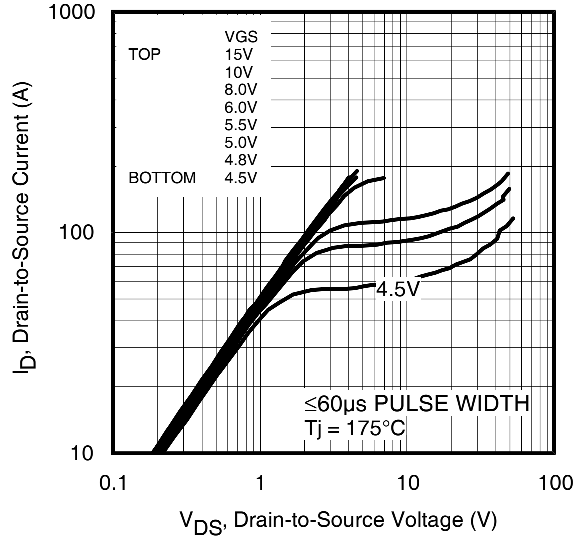


Fig 2. Typical Output Characteristics

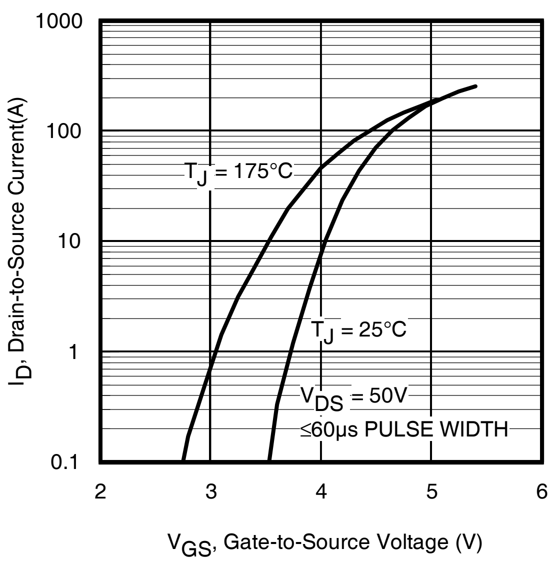


Fig 3. Typical Transfer Characteristics

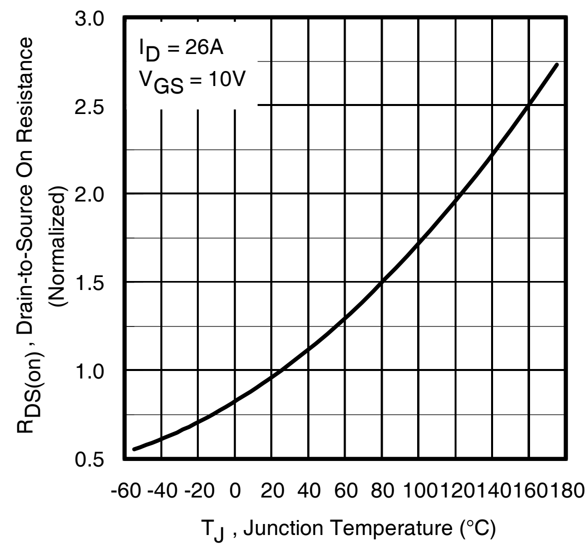


Fig 4. Normalized On-Resistance vs. Temperature

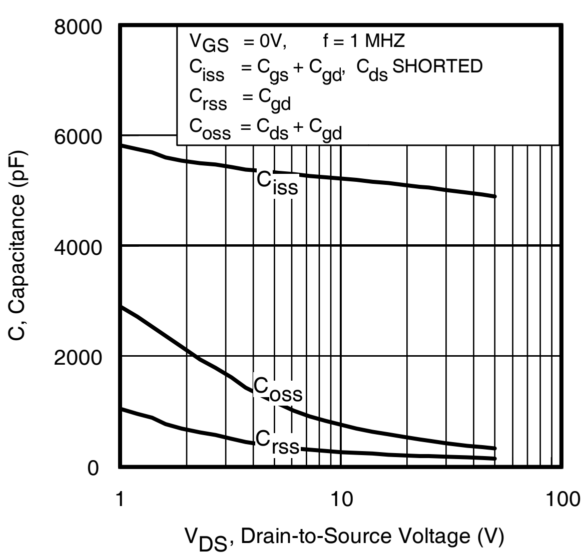


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

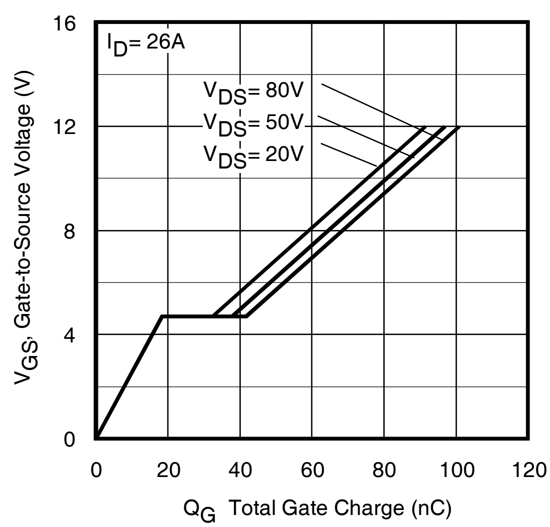


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

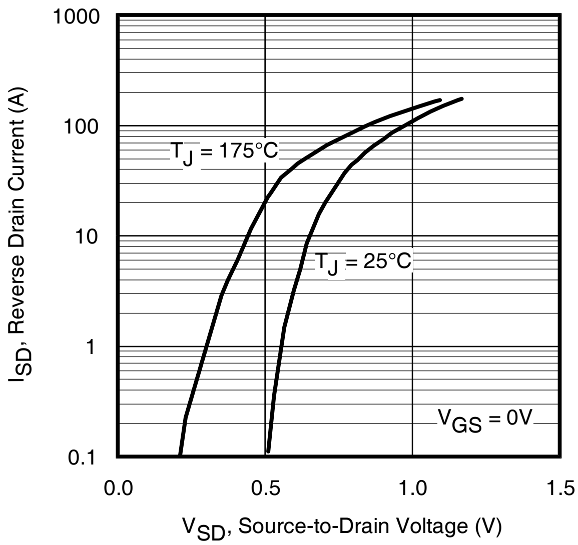


Fig 7. Typical Source-Drain Diode Forward Voltage

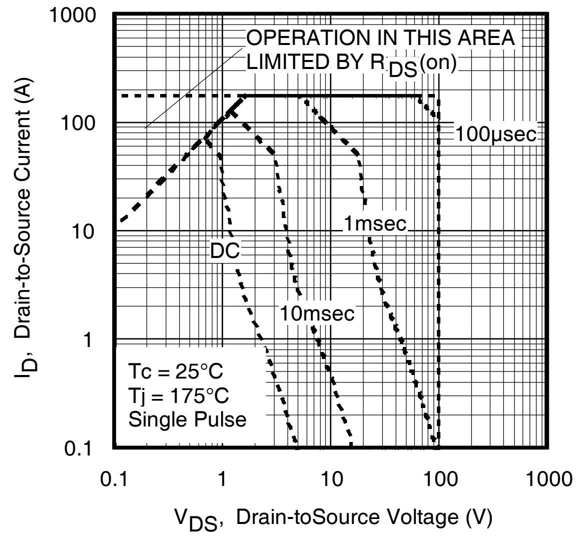


Fig 8. Maximum Safe Operating Area

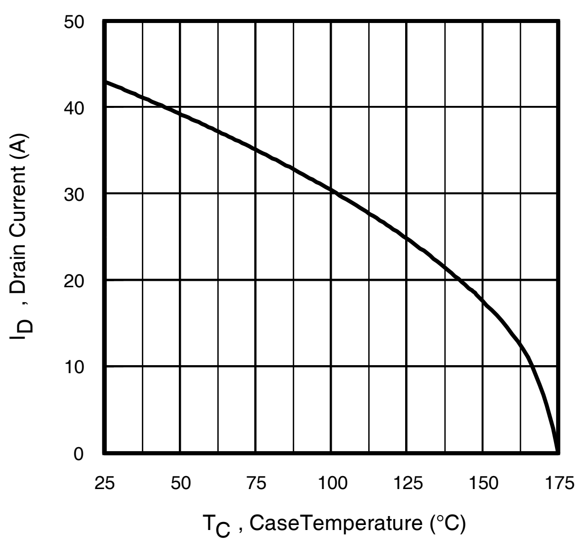


Fig 9. Maximum Drain Current vs. Case Temperature

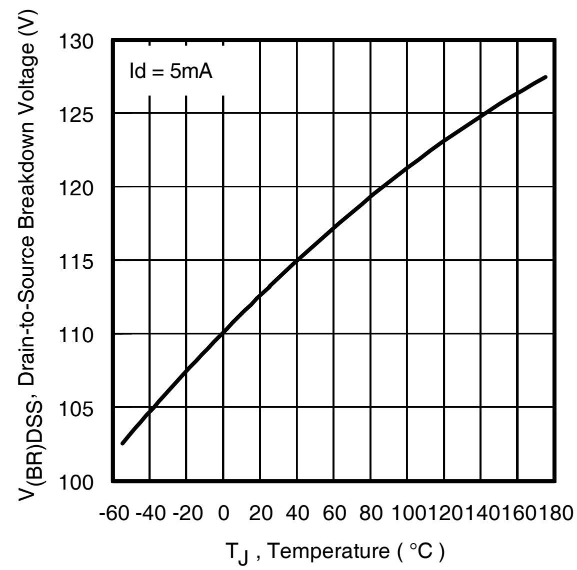


Fig 10. Drain-to-Source Breakdown Voltage

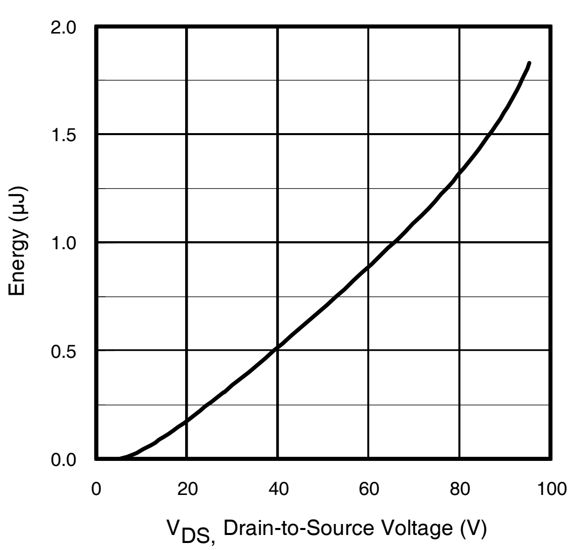


Fig 11. Typical C_{OSS} Stored Energy

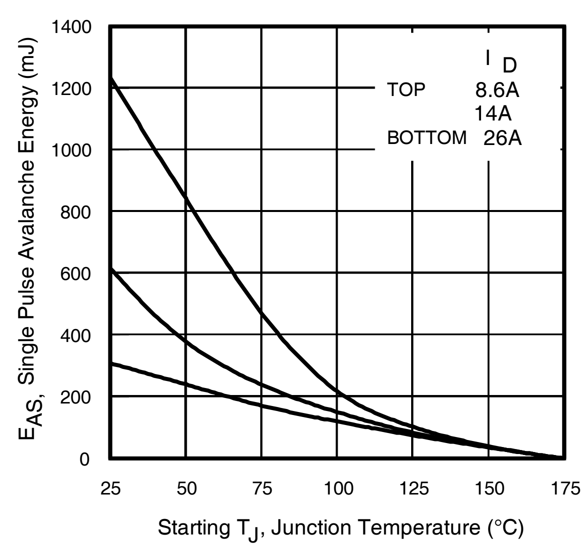


Fig 12. Maximum Avalanche Energy Vs. DrainCurrent

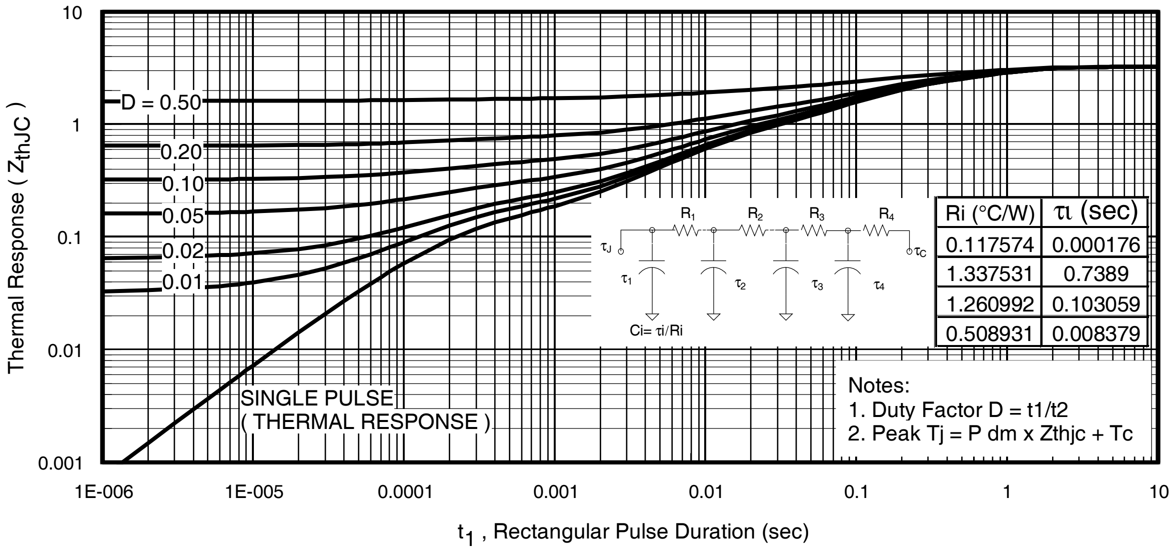


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

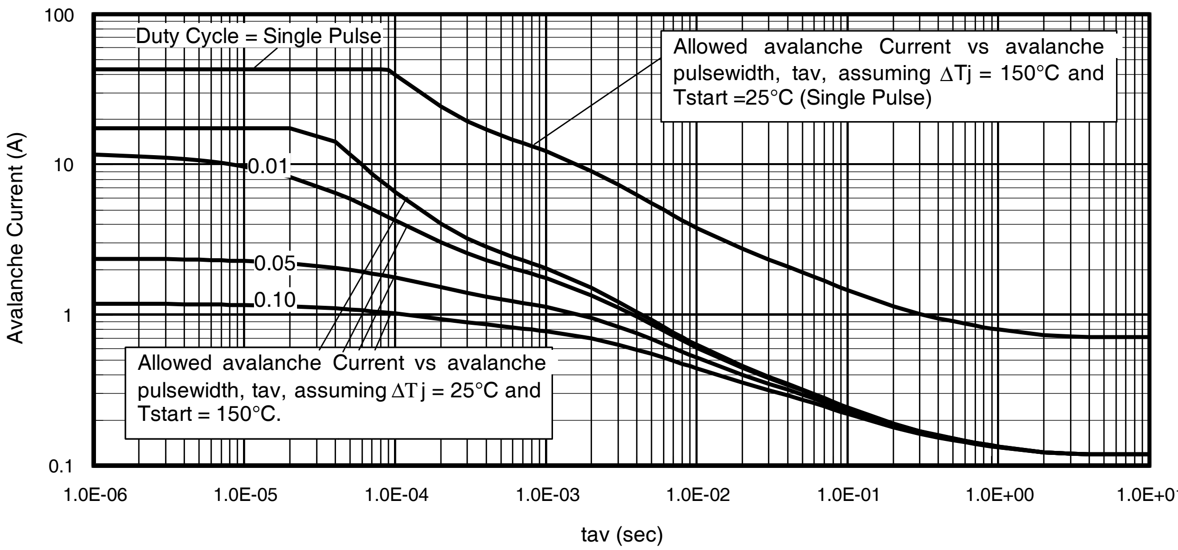


Fig 14. Typical Avalanche Current vs.Pulsewidth

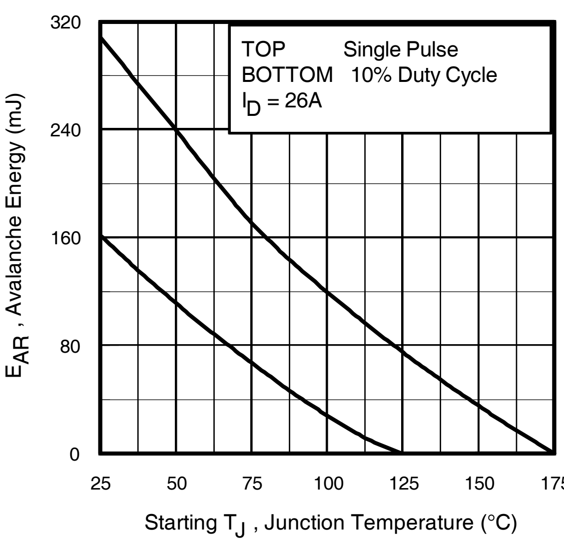


Fig 15. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
   Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 22a, 22b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
   t_{av} = Average time in avalanche.
   D = Duty cycle in avalanche = $t_{av} \cdot f$
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D\ (ave)} = 1/2\ (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$
$$E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}$$

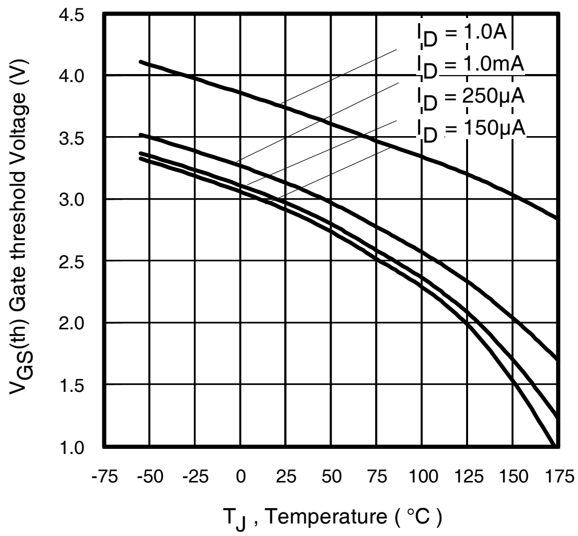


Fig 16. Threshold Voltage Vs. Temperature

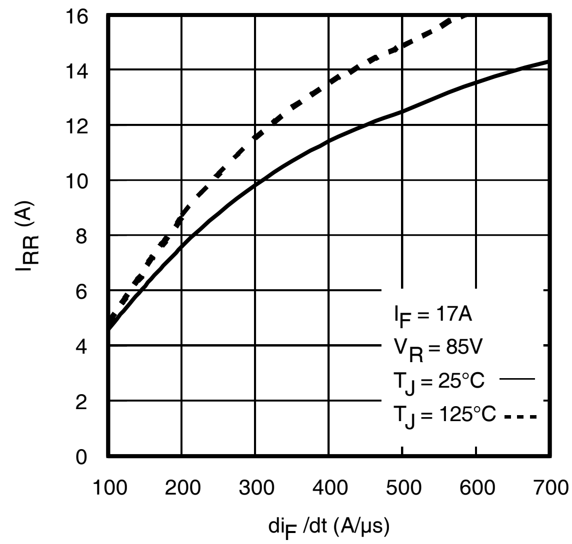


Fig. 17 - Typical Recovery Current vs. di_f/dt

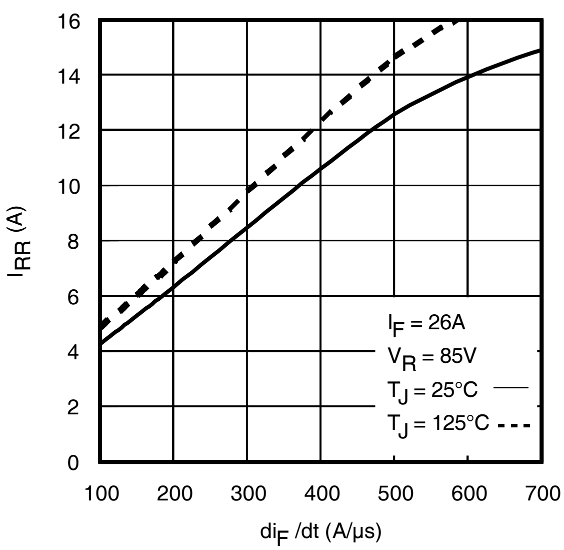


Fig. 18 - Typical Recovery Current vs. di_f/dt

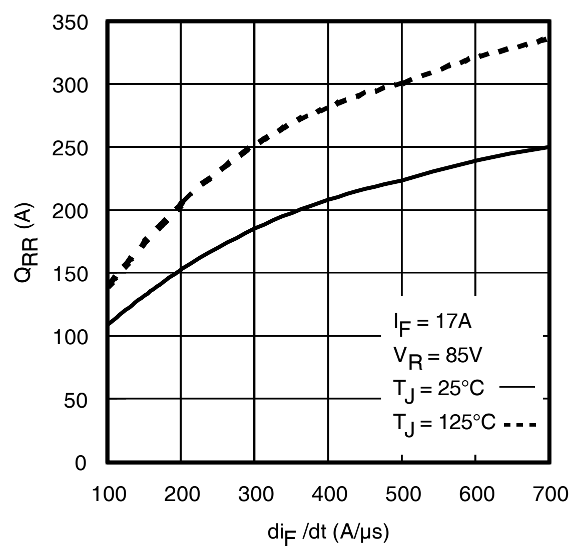


Fig. 19 - Typical Stored Charge vs. di_f/dt

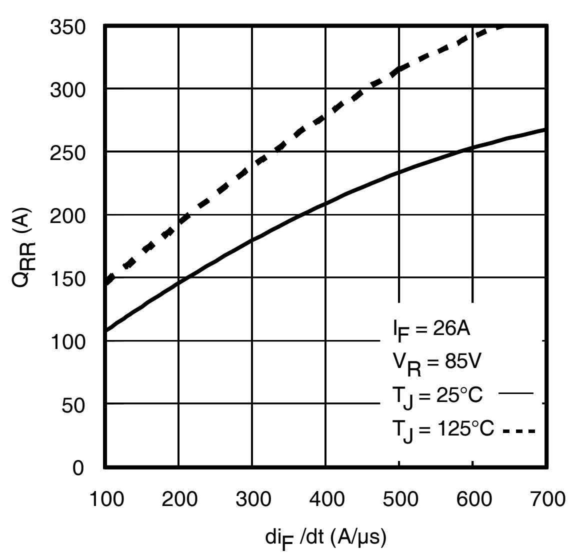
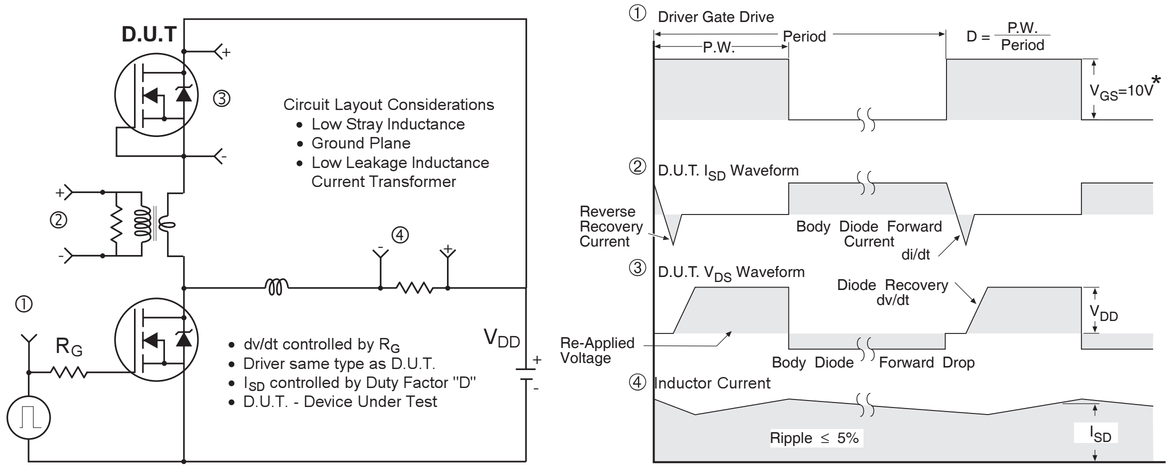


Fig. 20 - Typical Stored Charge vs. di_f/dt



* V_{GS} = 5V for Logic Level Devices

Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

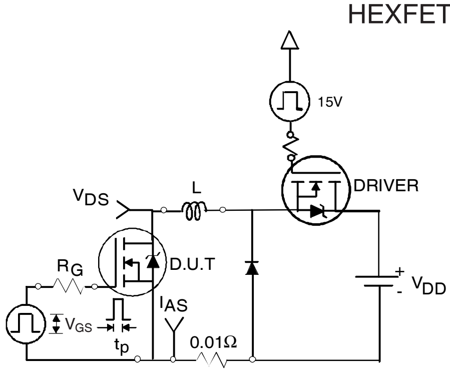


Fig 22a. Unclamped Inductive Test Circuit

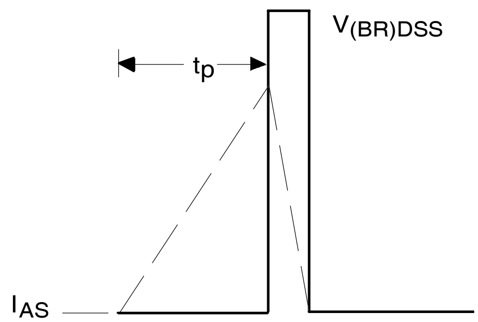


Fig 22b. Unclamped Inductive Waveforms

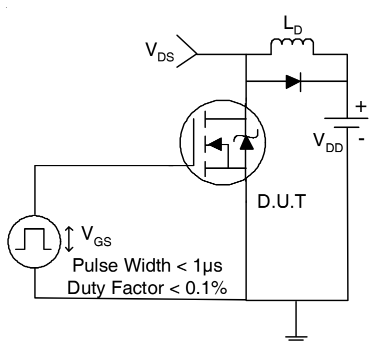


Fig 23a. Switching Time Test Circuit

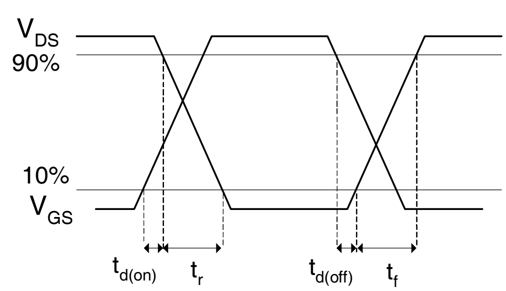


Fig 23b. Switching Time Waveforms

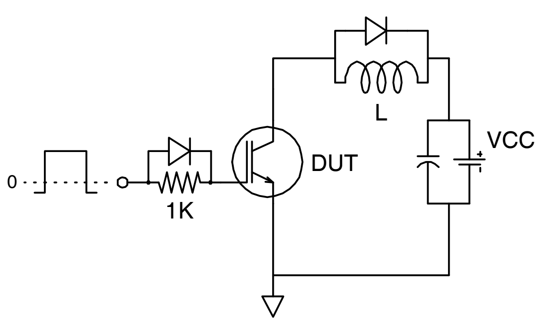


Fig 24a. Gate Charge Test Circuit

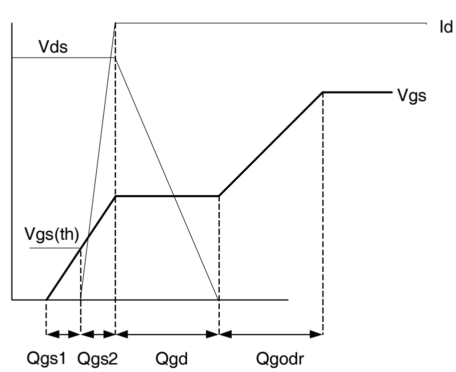
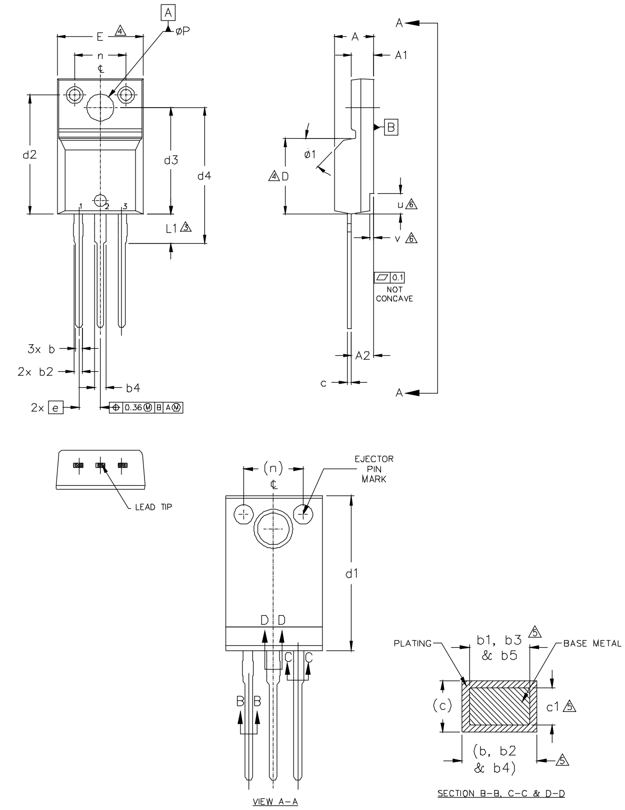


Fig 24b. Gate Charge Waveform

TO-220AB Full-Pak Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.
5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.
6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.57	4.83	.180	.190	
A1	2.57	2.83	.101	.111	
A2	2.41	2.92	.095	.115	
b	0.62	.094	0.24	.037	
b1	0.62	0.89	.024	0.35	5
b2	0.76	1.27	.030	.050	
b3	0.76	1.22	.030	.048	5
b4	1.02	1.52	.040	.060	
b5	1.02	1.47	.040	.058	5
c	0.33	0.63	.013	.025	
c1	0.33	0.58	.013	.023	5
D	8.65	9.80	.341	.386	4
d1	15.80	16.12	.622	.635	
d2	13.97	14.22	.550	.560	
d3	12.30	12.92	.484	.509	
d4	8.64	9.91	.340	.390	
E	9.63	10.63	.379	.419	4
e	2.54 BSC		.100 BSC		
L	13.20	13.72	.520	.540	
L1	3.10	2.31	.122	.138	3
n	6.05	6.15	.238	.242	
øP	3.05	3.45	.120	.136	
u	2.40	2.50	.094	.098	6
v	0.40	0.50	.016	.020	6
ø1	–	45°	–	45°	

LEAD ASSIGNMENTS

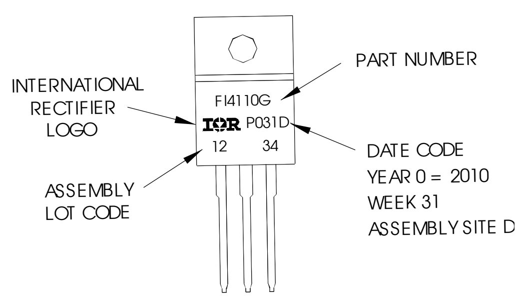
HEXFET
1.- GATE
2.- DRAIN
3.- SOURCE

IGBTs, CoPACK
1.- GATE
2.- COLLECTOR
3.- EMITTER

TO-220AB Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRFI4110G
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 31, 2010

Notes: - "P" in assembly line position indicates "Lead-Free"
- "G" suffix in part number indicates "Halogen-Free"



TO-220AB Full-Pak packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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